

Taiwan Semiconductor

# 10A, 45V - 200V Schottky Barrier Rectifier

### **FEATURES**

- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

## **APPLICATIONS**

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

## **MECHANICAL DATA**

- Case: TO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 1A whisker test
- Polarity: As marked
- Weight: 1.88g (approximately)

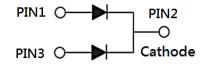
KEY PARAMETERS		
PARAMETER	VALUE	UNIT
I <sub>F</sub>	10	А
V <sub>RRM</sub>	45 - 200	V
I <sub>FSM</sub>	120	А
T <sub>J MAX</sub>	150	°C
Package	TO-220	DAB
Configuration	Dual d	lies











ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25	5°C unless ot	herwise r	noted)				
		MBR	MBR	MBR	MBR	MBR	
PARAMETER	SYMBOL	1045	1060	10100	10150	10200	UNIT
		CT-Y	CT-Y	CT-Y	CT-Y	CT-Y	
Marking code on the device		MBR 1045CT	MBR 1060CT	MBR 10100CT	MBR 10150CT	MBR 10200CT	
Repetitive peak reverse voltage	$V_{RRM}$	45	60	100	150	200	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	31	42	70	105	140	V
Forward current	I <sub>F</sub>			10			А
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>			120			Α
Peak repetitive reverse surge current <sup>(1)</sup>	I <sub>RRM</sub>	1		C	).5		А
Peak repetitive forward current (Rated V <sub>R</sub> , Square wave, 20KHz)	I <sub>FRM</sub>			10			А
Critical rate of rise of off-state voltage	dv/dt			10,000			V/µs
Junction temperature	$T_{J}$			-55 to +1	50		°C
Storage temperature	T <sub>STG</sub>			-55 to +1	50		°C

Notes:

1. tp = 2.0µs, 1.0KHz



THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	R <sub>eJC</sub>	1.5	°C/W

PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	MBR1045CT-Y	I <sub>F</sub> = 5A, T <sub>J</sub> = 25°C		-	0.70	V
	MBR1060CT-Y			-	0.80	V
	MBR10100CT-Y			-	0.85	V
	MBR10150CT-Y MBR10200CT-Y			-	0.88	V
	MBR1045CT-Y			-	0.80	V
	MBR1060CT-Y			-	0.90	V
	MBR10100CT-Y	I <sub>F</sub> = 10A, T <sub>J</sub> = 25°C		-	0.95	V
Forward voltage per	MBR10150CT-Y MBR10200CT-Y		N	-	0.98	V
diode <sup>(1)</sup>	MBR1045CT-Y	I <sub>F</sub> = 5A, T <sub>J</sub> = 125°C	V <sub>F</sub>	-	0.57	V
	MBR1060CT-Y			-	0.65	V
	MBR10100CT-Y			-	0.75	V
	MBR10150CT-Y MBR10200CT-Y		-	-	0.78	V
	MBR1045CT-Y	I <sub>F</sub> = 10A, T <sub>J</sub> = 125°C		-	0.67	V
	MBR1060CT-Y			-	0.75	V
	MBR10100CT-Y			-	0.85	V
	MBR10150CT-Y MBR10200CT-Y			-	0.88	V
Reverse current @ rated $V_R$ per diode <sup>(2)</sup>	MBR1045CT-Y MBR1060CT-Y MBR10100CT-Y MBR10150CT-Y MBR10200CT-Y	T <sub>J</sub> = 25°C		-	100	μA
	MBR1045CT-Y		I <sub>R</sub>	-	15	mA
	MBR1060CT-Y	T <sub>J</sub> = 125°C		-	10	mA
	MBR10100CT-Y			-	2	mA
	MBR10150CT-Y MBR10200CT-Y			-	5	mA

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE <sup>(1)</sup>	PACKAGE	PACKING
MBR10xCT-Y	TO-220AB	50 / Tube

Notes:

1. "x" defines voltage from 45V(MBR1045CT-Y) to 200V(MBR10200CT-Y)



**INSTANTANEOUS REVERSE CURRENT (mA)** 

# MBR1045CT-Y – MBR10200CT-Y

Taiwan Semiconductor

## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

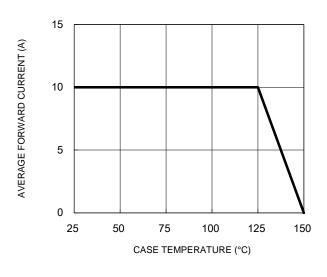
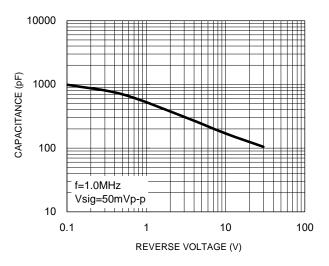


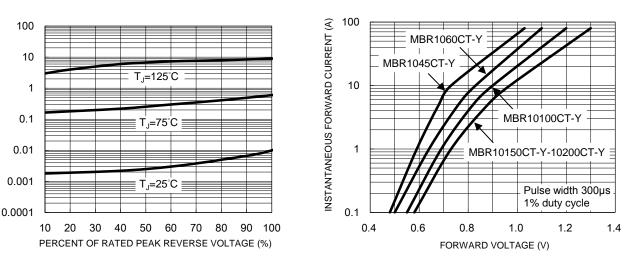
Fig.1 Forward Current Derating Curve

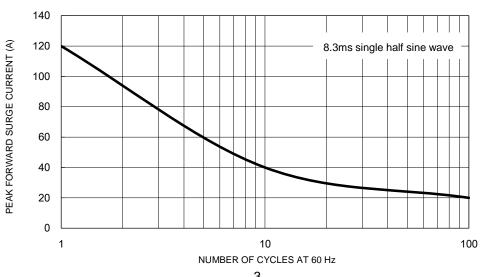
### **Fig.3 Typical Reverse Characteristics**



#### **Fig.2 Typical Junction Capacitance**

**Fig.4 Typical Forward Characteristics** 



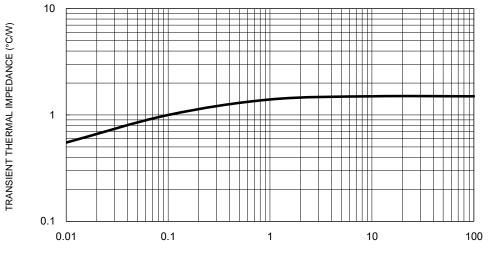


## Fig.5 Maximum Non-Repetitive Forward Surge Current



## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

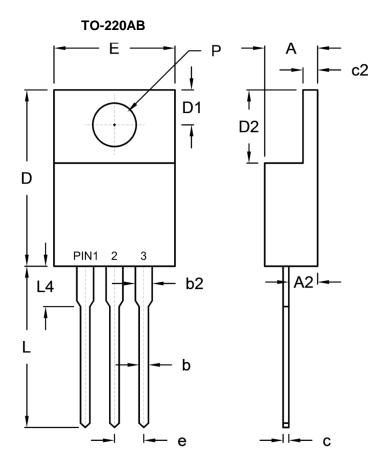


### Fig.6 Typical Transient Thermal Impedance

PULSE DURATION (s)

Taiwan Semiconductor

# PACKAGE OUTLINE DIMENSIONS



DIM.	Unit (mm)		Unit (	(inch)
	Min.	Max.	Min.	Max.
A	4.42	4.76	0.174	0.187
A2	2.20	2.80	0.087	0.110
b	0.68	0.94	0.027	0.037
b2	1.14	1.77	0.045	0.070
с	0.35	0.64	0.014	0.025
c2	1.14	1.40	0.045	0.055
D	14.60	16.00	0.575	0.630
D1	2.62	3.44	0.103	0.135
D2	5.84	6.86	0.230	0.270
E	-	10.50	-	0.413
е	2.41	2.67	0.095	0.105
L	13.19	14.79	0.519	0.582
L4	2.80	4.20	0.110	0.165
Р	3.54	4.00	0.139	0.157

## **MARKING DIAGRAM**



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



Taiwan Semiconductor

# Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf assumes no responsibility or liability for any errors or inaccuracies.

Purchasers are solely responsible for the choice, selection, and use of TSC products and TSC assumes no liability for application assistance or the design of Purchasers' products.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.